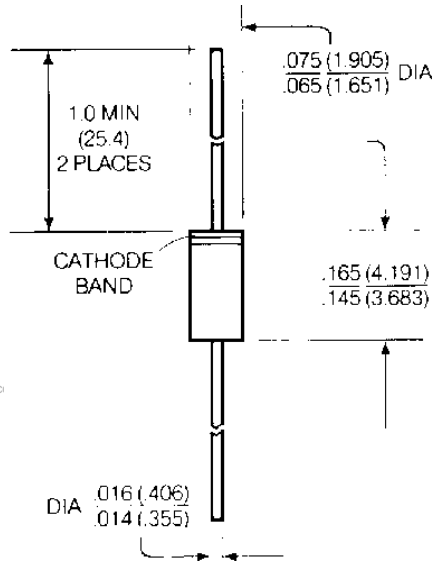
SILICON PIN DIODE

DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

PACKAGE STYLE 01



MAXIMUM RATINGS

I_C	100 mA
V_{CE}	300 V
P_{DISS}	250 mW @ T_A = 25 ^{O}C
T_J	-65 ^{O}C to +175 ^{O}C
T_{STG}	-65 ^{O}C to +175 ^{O}C
θ_{JC}	20 ^{O}C/W

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I_R = 10 µA	300			V
C_J	V_R = 50 V f = 1.0 MHz V_R = 40 V			0.2	pF
C_P	f = 1.0 MHz		0.10		pF
L_S			1.0		nH
R_S	I_F = 50 mA f = 100 MHz			0.6	Ohms
T_L	I_F = 10 mA I_R = 6.0 mA		1000		nS
T_{rr}	I_F = 20 mA I_R = 100 mA @ 90%		100		nS
I-REGION			30		µM